


Full Bridge TrenchStop IGBT, MTP Power Modules



MTP
(Package example)

FEATURES

- TrenchStop IGBT technology
- Positive $V_{CE(on)}$ temperature coefficient
- FRED Pt® Gen5 antiparallel diodes with ultrasoft reverse recovery
- Low diode V_F
- Square RBSOA
- Very low stray inductance design for high speed operation
- UL approved file E78996 
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

PRIMARY CHARACTERISTICS

V_{CES}	600 V
I_C at $T_C = 45\text{ }^{\circ}\text{C}$	50 A
$V_{CE(on)}$ at 50 A	1.81 V
Speed	30 kHz to 100 kHz
Package	MTP
Circuit configuration	Full bridge

BENEFITS

- Optimized for welding, UPS and SMPS applications
- Rugged with ultrafast performance
- Outstanding ZVS and hard switching operation
- Low EMI, requires less snubbing
- Excellent current sharing in parallel operation
- Direct mounting to heatsink
- PCB solderable terminals
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter breakdown voltage	V_{CES}		600	V
Continuous collector current	I_C	$T_C = 25\text{ }^{\circ}\text{C}$	55	A
		$T_C = 80\text{ }^{\circ}\text{C}$	41	
Pulsed collector current	I_{CM}	$V_{GE} = 15\text{ V}$	115	
Clamped inductive load current	I_{LM}		95	
Diode continuous forward current	I_F	$T_C = 25\text{ }^{\circ}\text{C}$	54	
		$T_C = 80\text{ }^{\circ}\text{C}$	41	V
Diode maximum forward current	I_{FM}		250	
Gate to emitter voltage	V_{GE}		± 20	V
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1\text{ min}$	2500	
Maximum power dissipation (only IGBT)	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	144	W
		$T_C = 80\text{ }^{\circ}\text{C}$	91	
Maximum power dissipation (only diode)	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	107	
		$T_C = 80\text{ }^{\circ}\text{C}$	68	


ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$, $I_C = 0.5\text{ mA}$	600	-	-	V
Collector to emitter saturation voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$	-	1.81	2.1	$V_{CE(on)}$
		$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2.1	-	
		$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$	-	2.23	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 0.5\text{ mA}$	2.8	4.0	5.3	
Temperature coefficient of threshold voltage	$V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, $I_C = 0.5\text{ mA}$ ($25\text{ }^{\circ}\text{C}$ to $125\text{ }^{\circ}\text{C}$)	-	-9.9	-	mV/ $^{\circ}\text{C}$
Transconductance	g_{fe}	$V_{CE} = 20\text{ V}$, $I_C = 50\text{ A}$	-	37	-	S
Transfer characteristics	V_{GE}	$V_{CE} = 20\text{ V}$, $I_C = 50\text{ A}$	-	6.4	-	V
Zero gate voltage collector current	$I_{CES}^{(1)}$	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	0.3	40	μA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	40	-	mA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 175\text{ }^{\circ}\text{C}$	-	1.2	-	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 200	nA

Note

 (1) I_{CES} includes also opposite leg overall leakage

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 50\text{ A}$ $V_{CC} = 520\text{ V}$ $V_{GE} = 15\text{ V}$	-	123	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	20	-	
Gate to collector charge (turn-on)	Q_{gc}		-	24	-	
Turn-on switching loss	E_{on}	$V_{CC} = 300\text{ V}$, $I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$, $R_g = 4.7\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	0.37	-	mJ
Turn-off switching loss	E_{off}		-	0.23	-	
Total switching loss	E_{tot}		-	0.70	-	
Turn-on switching loss	E_{on}	$V_{CC} = 300\text{ V}$, $I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$, $R_g = 4.7\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	0.53	-	
Turn-off switching loss	E_{off}		-	0.31	-	
Total switching loss	E_{tot}		-	0.84	-	
Input capacitance	C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$ $T_J = 25\text{ }^{\circ}\text{C}$	-	3000	-	pF
Output capacitance	C_{oes}		-	50	-	
Reverse transfer capacitance	C_{res}		-	11	-	
Reverse bias safe operating area	RBSOA	$T_J = 175\text{ }^{\circ}\text{C}$, $I_C = 95\text{ A}$, $R_g = 4.7\text{ }\Omega$, $V_{GE} = 15\text{ V}$ to 0 V , $V_{CC} = 300\text{ V}$, $V_p = 600\text{ V}$	Fullsquare			

DIODE SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Diode forward voltage drop	V_{FM}	$I_C = 50\text{ A}$	-	1.66	2.23	V
		$I_C = 50\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.43	-	
		$I_C = 50\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$	-	1.32	-	
Diode reverse recovery time	t_{rr}	$V_R = 400\text{ V}$, $I_F = 30\text{ A}$, $dI/dt = 1000\text{ A}/\mu\text{s}$	-	61	-	ns
Diode peak reverse current	I_{rr}		-	16	-	A
Diode recovery charge	Q_{rr}		-	400	-	nC
Diode reverse recovery time	t_{rr}	$V_R = 400\text{ V}$, $I_F = 30\text{ A}$, $dI/dt = 1000\text{ A}/\mu\text{s}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	68	-	ns
Diode peak reverse current	I_{rr}		-	33	-	A
Diode recovery charge	Q_{rr}		-	1300	-	nC

INTERNAL NTC - THERMISTOR SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNITS
Resistance	R_{25}	$T_J = 25\text{ }^{\circ}\text{C}$	5000	Ω
	R_{100}	$T_J = 100\text{ }^{\circ}\text{C}$	$493 \pm 5\%$	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp. [B_{25/50} (1/T_2 - 1/298.15K)]$	$3375 \pm 5\%$	K
Maximum operating temperature			220	$^{\circ}\text{C}$
Dissipation constant			2	mW/ $^{\circ}\text{C}$
Thermal time constant			8	s

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	T_J		-40	-	175	$^{\circ}\text{C}$
Storage temperature range	T_{Stg}		-40	-	150	
Junction to case	R_{thJC}	IGBT	-	-	1.04	$^{\circ}\text{C/W}$
		Diode	-	-	1.40	
Case to sink per module	R_{thCS}	Heatsink compound thermal conductivity = 1 W/mK	-	0.06	-	$^{\circ}\text{C/W}$
Clearance		External shortest distance in air between two terminals	5.5	-	-	mm
Creepage		Shortest distance along external surface of the insulating material between two terminals	8	-	-	
Mounting torque		A mounting compound is recommended and the torque should be checked after 3 hours to allow for the spread of the compound. Lubricated threads.	$3 \pm 10\%$			Nm
Weight			66			g

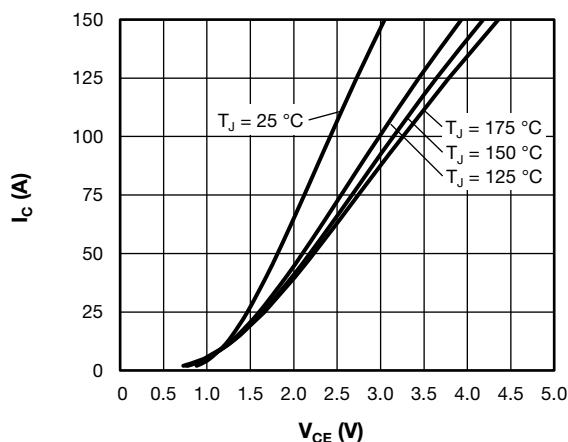


Fig. 1 - Typical Q1 to Q4 IGBT Output Characteristics, $V_{GE} = 15\text{ V}$

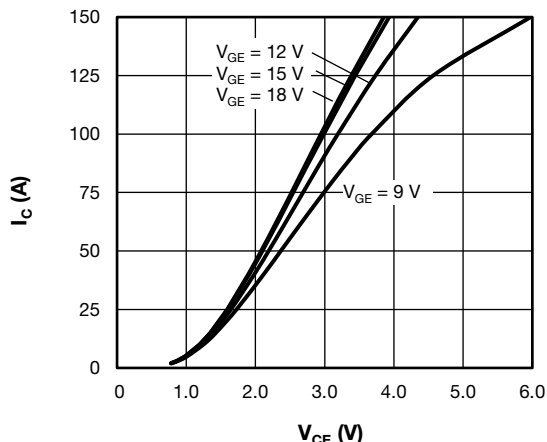


Fig. 2 - Typical Q1 to Q4 IGBT Output Characteristics, $T_J = 125\text{ }^{\circ}\text{C}$

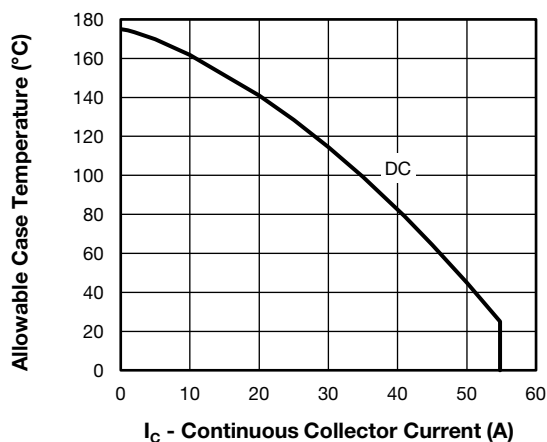


Fig. 3 - Maximum Q1 to Q4 IGBT Continuous Collector Current vs. Case Temperature

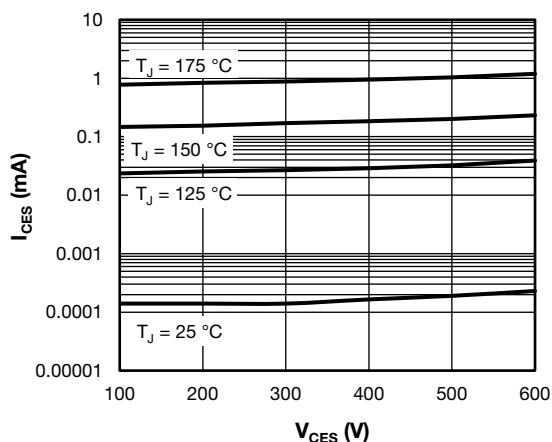


Fig. 6 - Typical Q1 to Q4 IGBT Zero Gate Voltage Collector Current

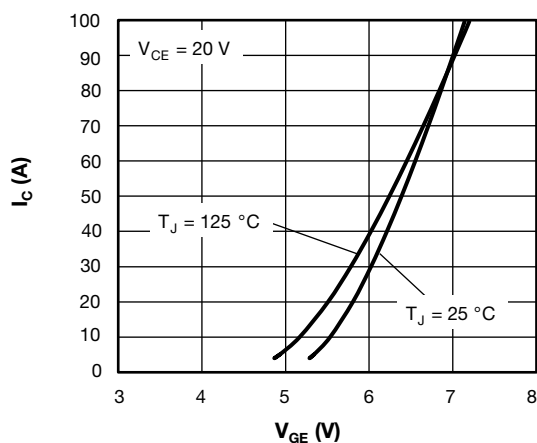


Fig. 4 - Typical Q1 to Q4 IGBT Transfer Characteristics

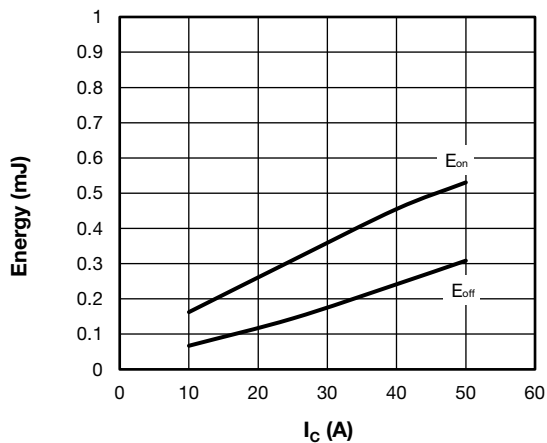


Fig. 7 - Typical Q1 to Q4 IGBT Energy Loss vs. I_C (with Antiparallel Diode)
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

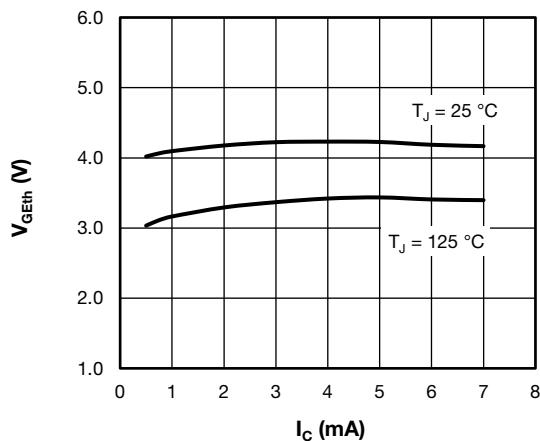


Fig. 5 - Typical Q1 to Q4 IGBT Gate Threshold Voltage

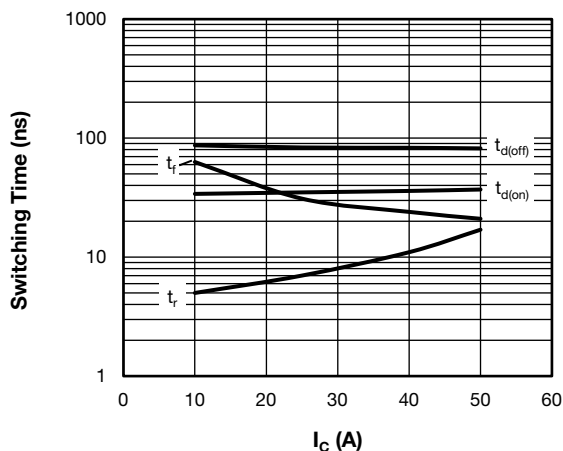


Fig. 8 - Typical Q1 to Q4 IGBT Switching Time vs. I_C (with Antiparallel Diode)
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\ \mu\text{H}$

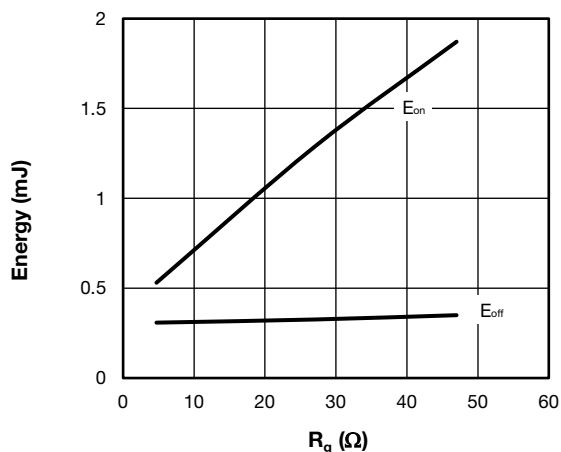


Fig. 9 - Typical Q1 to Q4 IGBT Energy Loss vs. R_g (with Antiparallel Diode)

$T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 50\text{ A}$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\text{ }\mu\text{H}$

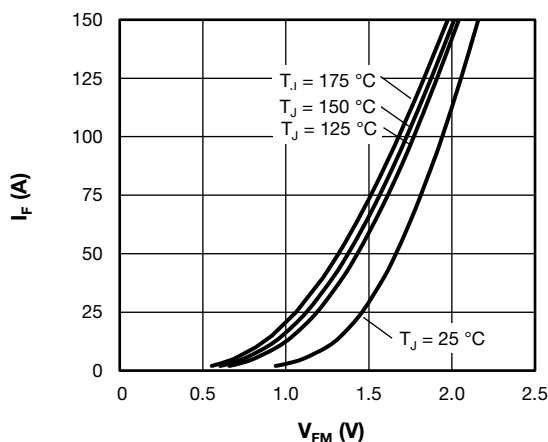


Fig. 12 - Typical D1 to D4 Antiparallel Diode Forward Characteristics

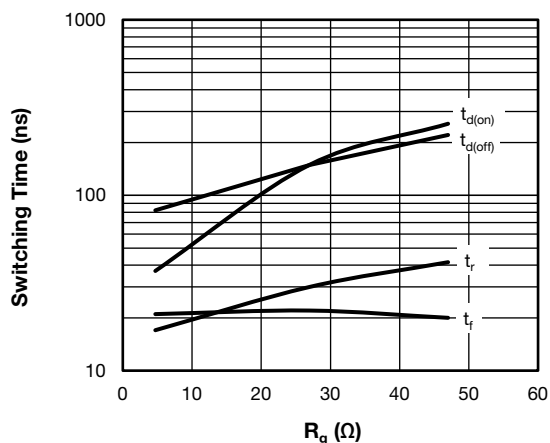


Fig. 10 - Typical Q1 to Q4 IGBT Switching Time vs. R_g (with Antiparallel Diode)

$T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 50\text{ A}$, $V_{GE} = +15\text{ V}/-15\text{ V}$, $L = 500\text{ }\mu\text{H}$

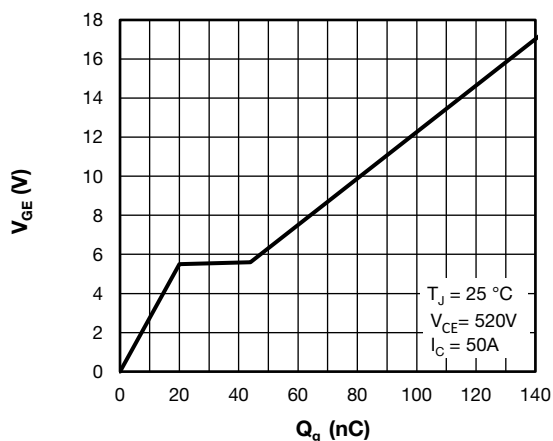


Fig. 11 - Typical Q1 to Q4 IGBT Gate Charge vs. Gate to Emitter Voltage

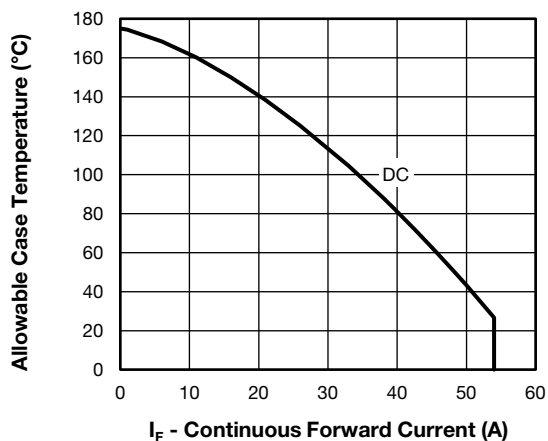


Fig. 13 - Maximum D1 to D4 Antiparallel Diode Continuous Collector Current vs. Case Temperature

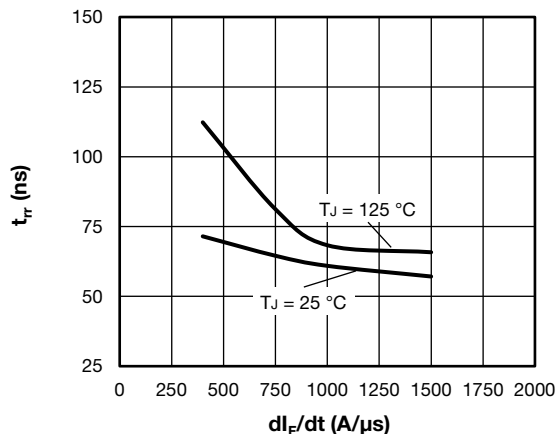


Fig. 14 - Typical D1 to D4 Antiparallel Diode Reverse Recovery Time vs. di_F/dt
 $V_{rr} = 400\text{ V}$, $I_F = 30\text{ A}$

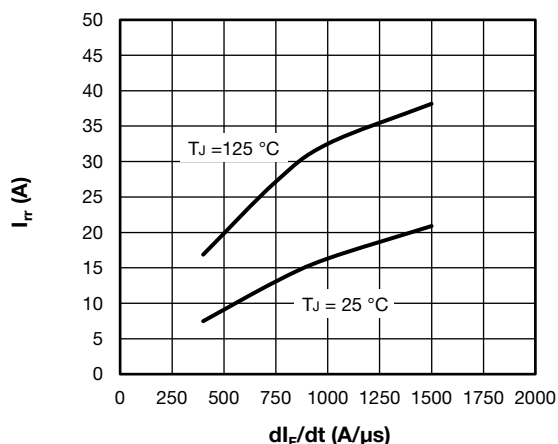


Fig. 15 - Typical D1 to D4 Antiparallel Diode Reverse Recovery Current vs. di_F/dt
 $V_{rr} = 400 \text{ V}$, $I_F = 30 \text{ A}$

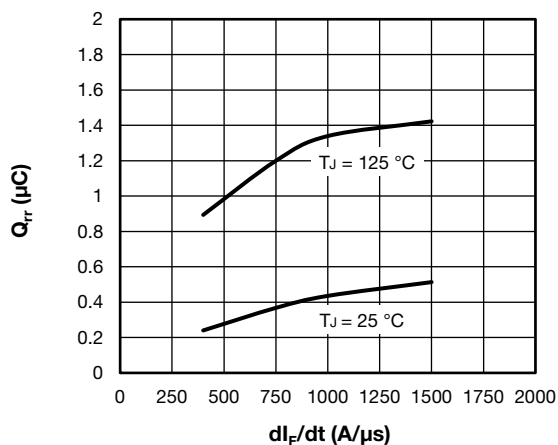


Fig. 16 - Typical D1 to D4 Antiparallel Diode Reverse Recovery Charge vs. di_F/dt
 $V_{rr} = 400 \text{ V}$, $I_F = 30 \text{ A}$

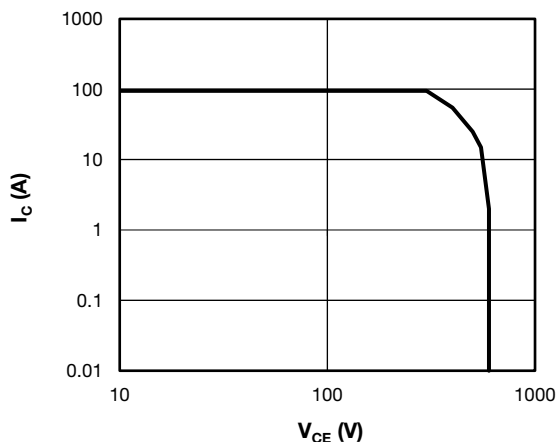


Fig. 17 - Q1 to Q4 IGBT Reverse BIAS SOA
 $T_J = 175 \text{ °C}$, $I_C = 95 \text{ A}$, $R_g = 4.7 \text{ } \Omega$, $V_{GE} = +15 \text{ V/0 V}$, $V_{CC} = 300 \text{ V}$, $V_p = 600 \text{ V}$

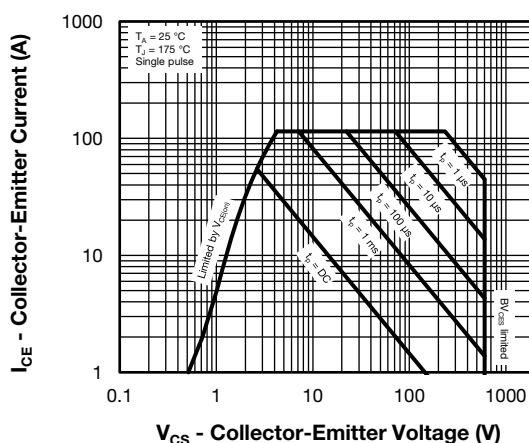


Fig. 18 - Q1 to Q4 IGBT Safe Operating Area

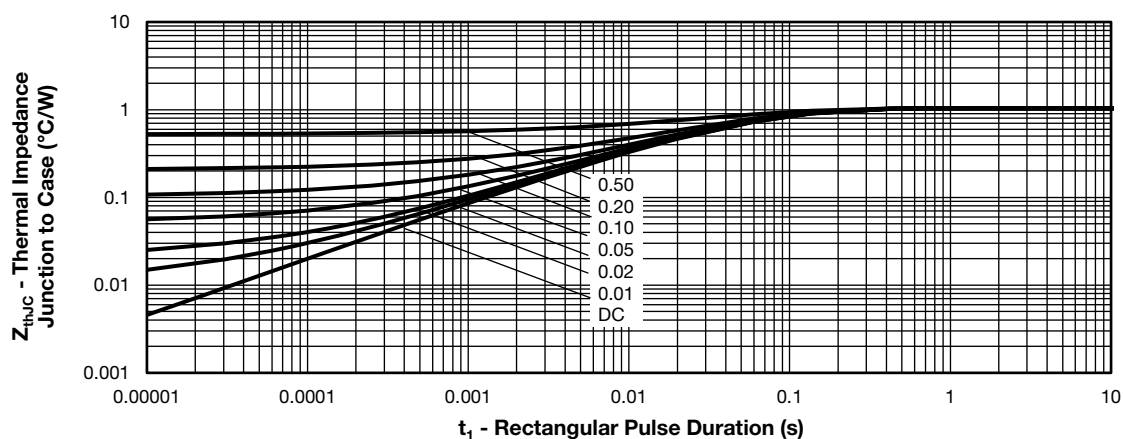


Fig. 19 - Maximum Thermal Impedance Z_{thJC} Characteristics - (Q1 to Q4 PT IGBT)

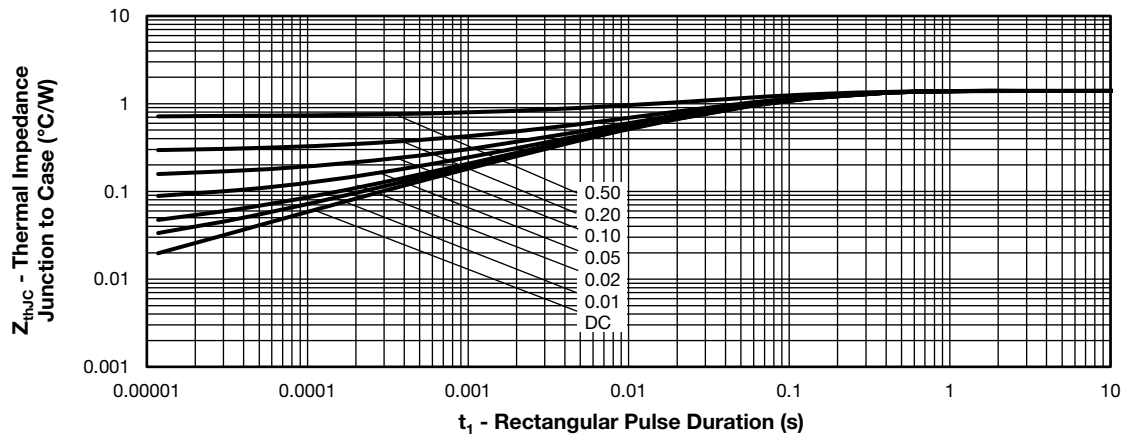


Fig. 20 - Maximum Thermal Impedance Z_{thJC} Characteristics - (D1 to D4 Antiparallel Diode)

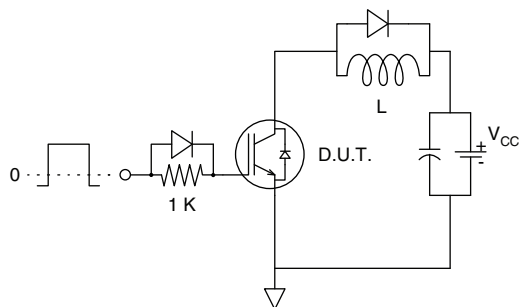


Fig. 21 - Gate Charge Circuit (Turn-Off)

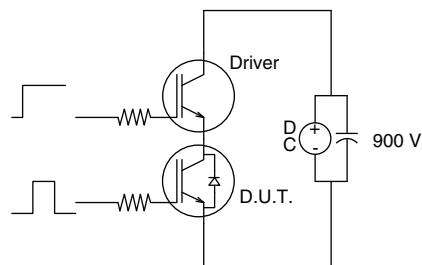


Fig. 23 - S.C. SOA Circuit

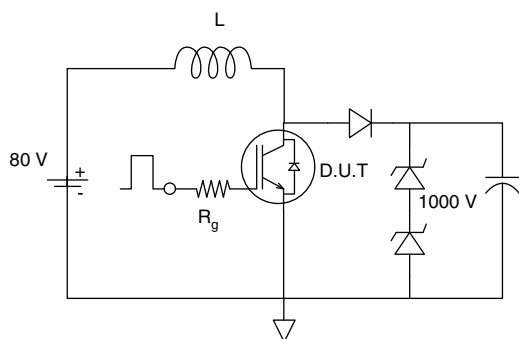


Fig. 22 - RBSOA Circuit

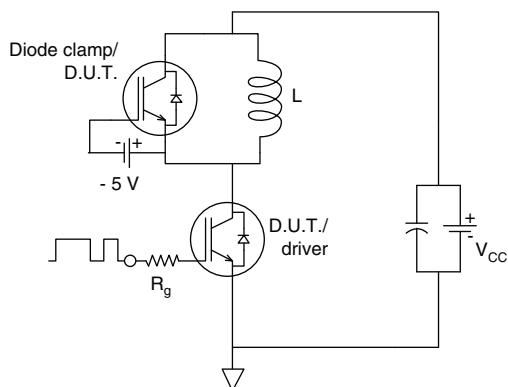
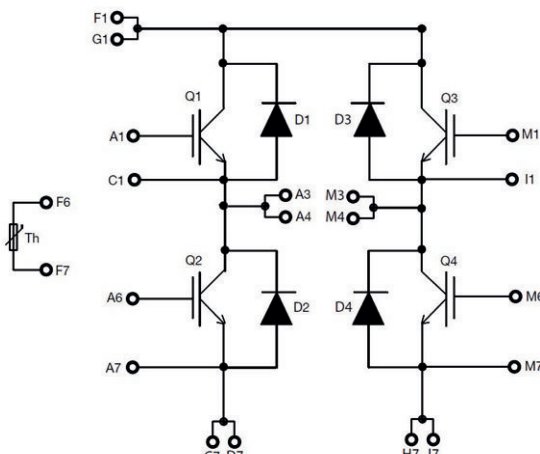


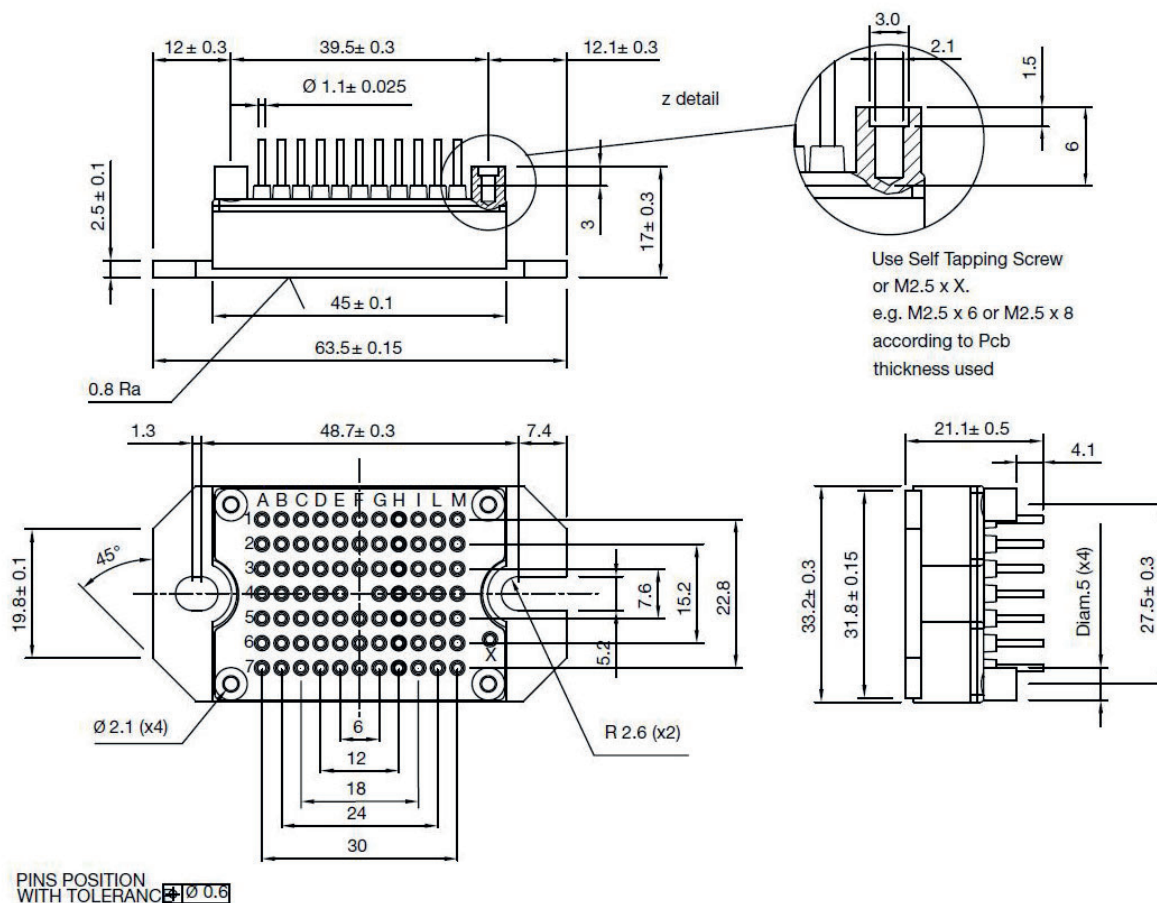
Fig. 24 - Switching Loss Circuit

ORDERING INFORMATION TABLE

Device code	VS-	50	MT	060	T	F	T
	1	2	3	4	5	6	7
1	Vishay Semiconductors product						
2	Current rating (50 = 50 A)						
3	Essential part number						
4	Voltage code (060 = 600 V)						
5	Speed / type (T = trench IGBT)						
6	Circuit configuration (F = full bridge)						
7	T = thermistor						

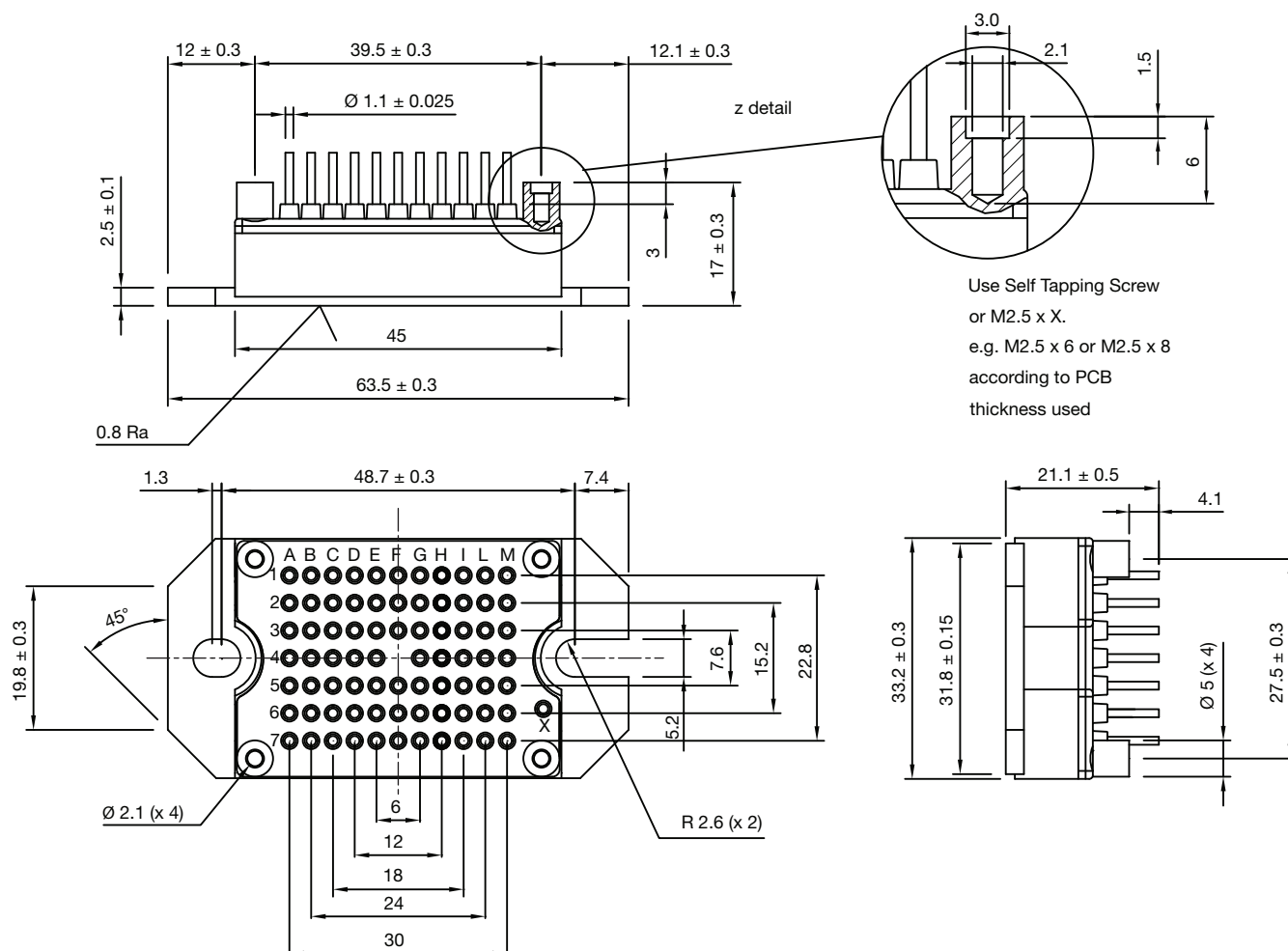
CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Full bridge IGBT	F	

DIMENSIONS in millimeters



MTP - Full Pin

DIMENSIONS in millimeters



PINS POSITION
WITH TOLERANCE $\varnothing 0.6$

Tolerance (unless other stated):

 $X = \pm 0.3$
$$X.X = \pm 0.1$$
$$X.XX = \pm 0.03$$



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